

### MicroNote 104

## Using the Power vs. Time Curve

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The maximum transient power and current capability of a silicon transient voltage suppressor (TVS) can be derived for conditions other than the 10/1000 µs pulse specified on datasheets by using its peak pulse power versus pulse time curve.

Most TVSs are rated for 10/1000 μs non-repetitive pulses—10 μs being the rise time and 1000 μs being the time to decay to one-half peak value—based on an early telecom specification. Real world conditions produce a vast array of waveforms having pulse widths ranging from tens of nanoseconds to tens of milliseconds in duration. For example, IEC 801-5 describes 1.2/50 µs lightning threats to signal lines.

The graph in Figure 1 (see page 1) relates peak pulse power versus time for 600 W suppressors. Similar graphs depict power versus time for TVSs rated at other power levels. At 1000 μs, the maximum peak pulse power (Ppp) for this series is 600 W (the device rating).

For short pulse widths, the TVS will sustain higher peak pulse currents (IPP). As the graph illustrates, at 20 us, the PPP rating is 3.2 kW (or 5.3 times its rating at 1000 µs). Hence the IPP rating of an SMBJ12C would increase by a factor of 5.3 from 27.3 A to 145 A for a 20 µs pulse.

For longer pulses, the TVS will withstand lower IPP values. At 10.000 us (10 ms), PPP rating is down to approximately 200 W, one-third of its 1000 µs rating. The IPP for an SMBJ12C would be reduced by a factor of .33, from 27.3 A to 9.1 A for a 10,000 µs pulse. This applies to all devices in the 600 W series regardless of their operating voltage.

In the same manner, the PPP and/or IPP can be derived for a component of any other TVS series using its associated power versus time curve.

Most silicon TVSs are rated for 10/1000 µs double exponential waveforms, including the example shown here. For one-half sine wave pulses, derate to 75% of the peak exponential value and for square wave pulses derate to 66%. Further information on this subject is available in MicroNote 120.



Figure 1: Peak Pulse Power vs. Pulse Time

(P<sub>PP</sub>) - Peak Pulse Power 10 1.0 1 µs 10 us 100 µs 1<sub>ms</sub> 10<sub>ms</sub> t<sub>p</sub> − Pulse Time − seconds



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